



Micro Commercial Components  
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# 2SD845

## NPN Silicon Power Transistors

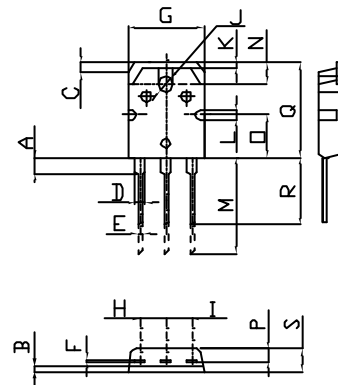
### Features

- With TO-3P(I) package
- Recommended for 60-80W high-fidelity frequency amplifier output stage

### Maximum Ratings

Symbol	Rating	Rating	Unit
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current	12	A
$P_C$	Collector power dissipation	120	W
$T_J$	Junction Temperature	-55 to +150	$^{\circ}C$
$T_{STG}$	Storage Temperature	-55 to +150	$^{\circ}C$

### TO-3P(I)



### Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
<b>OFF CHARACTERISTICS</b>				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ( $I_C=50mA_{dc}$ , $I_B=0$ )	150	---	Vdc
$I_{CBO}$	Collector-Base Cutoff Current ( $V_{CB}=150V_{dc}$ , $I_E=0$ )	---	50	$\mu A_{dc}$
$I_{EBO}$	Emitter-Base Cutoff Current ( $V_{EB}=5.0V_{dc}$ , $I_C=0$ )	---	50	$\mu A_{dc}$
<b>ON CHARACTERISTICS</b>				
$h_{FE}$	Forward Current Transfer ratio ( $I_C=1.0A_{dc}$ , $V_{CE}=5.0V_{dc}$ )	100	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C=5.0A_{dc}$ , $I_B=0.5A_{dc}$ )	---	2.0	Vdc

DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	---	.130	---	3.30	
B	---	.071	---	1.80	
C	.079		2.00		
D	.067	.091	1.70	2.30	
E	.030	.051	.75	1.30	
F	.012	.028	.30	.70	
G	---	.626	---	15.90	
H	.205	.220	5.20	5.60	
I	.207	.222	5.25	5.65	
J	.118	.134	3.00	3.40	∅
K	.039		1.00		
L	.079		2.00		
M	.748	.827	19.00	21.00	
N	.177		4.50		
O	.354		9.00		
P	.110		2.80		
Q	.067	.091	1.70	2.30	
R	.512	.551	13.00	14.00	
S	---	.189	---	4.80	